

ABSTRACT OF THE DISCLOSURE

Disclosed is a semiconductor device comprising
a semiconductor substrate, a capacitor provided above
the semiconductor substrate and including a bottom
5 electrode, a top electrode, and a dielectric film
provided between the top electrode and the bottom
electrode, an insulating region surrounding the
capacitor and having a first hole which extends in
a vertical direction and reaches the top electrode and
10 a second hole which extends in the vertical direction
and is spaced away from the capacitor, and a first
wiring connected to the top electrode and including
a first conductive portion formed in the first hole and
a second conductive portion formed in the second hole,
15 the first wiring having a barrier metal film between
the insulating region and the first conductive portion
and having no barrier metal film between the insulating
region and the second conductive portion.